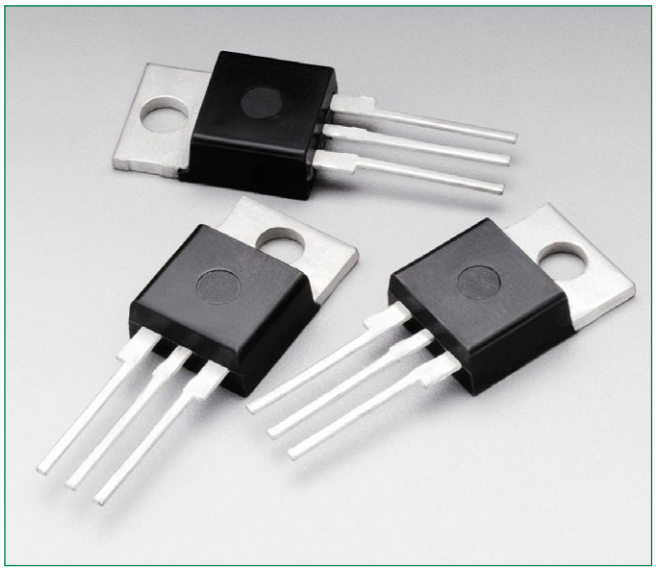
MCR218-2G, MCR218-4G, MCR218-6G



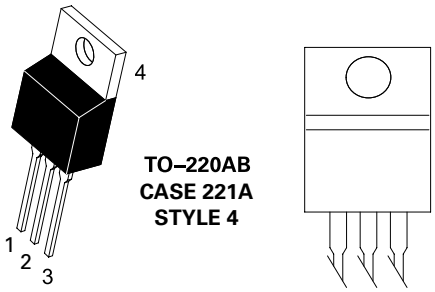
Description

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

Features

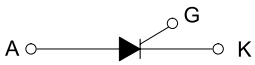
- Glass-Passivated Junctions
- Blocking Voltage to 400 Volts
- TO-220 Construction – Low Thermal Resistance, High Heat Dissipation and Durability

Pin Out



TO–220AB
CASE 221A
STYLE 4

Functional Diagram



Additional Information

Datasheet | **Resources** | **Samples**

Revised: 07/15/19

Maximum Ratings (T_J = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (– 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	MCR68-2	V_{DRM}, V_{RRM}	50	V
On-State RMS Current (180° Conduction Angles; T_C = 85°C)		$I_{TM\ (RMS)}$	12	A
Peak Discharge Current (Note 2)		I_{TM}	300	A
Average On-State Current (180° Conduction Angles; T_C = 85°C)		$I_{T(AV)}$	8.0	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T_J = 125°C)		I_{TSM}	100	A
Circuit Fusing Consideration (t = 8.3 ms)		I^2t	40	A^2sec
Forward Peak Gate Current (Pulse Width ≤ 1.0 µsec, T_C= 80°C)		I_{GM}	2.0	A
Forward Peak Gate Current (Pulse Width ≤ 1.0 µsec, T_C= 85°C)		I_{GM}	20	W
Forward Average Gate Power (t = 8.3 ms, TC = 85°C)		$P_{G(AV)}$	0.5	W
Operating Junction Temperature Range		T_J	-40 to +125	°C
Storage Temperature Range		T_{stg}	-40 to +150	°C
Mounting Torque		–	8.0	in. lb.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. Ratings apply for tw = 1 ms. See Figure 1 for I_{TM} capability for various duration of an exponentially decaying current waveform, tw is defined as 5 time constants of an exponentially decaying current pulse.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction–to–Case (AC) Junction–to–Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 60	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		T_L	260	°C

Electrical Characteristics - OFF (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Peak Repetitive Forward or Reverse Blocking Current (VD = Rated VDRM and VRRM; Gate Open)	T_J = 25°C	I_{DRM}, I_{RRM}	-	-	10	mA
	T_J = 125°C		-	-	2.0	

Electrical Characteristics - ON (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Peak Forward On–State Voltage (Note 2)	(I_{TM} = 32 A)(I_{TM} = 24 A) (Note 3) (I_{TM} = 300 A, tw = 1 ms) (Note 4)	V_{TM}	– –	– 6.0	2.2 –	V
Gate Trigger Current (Continuous dc) (V_D = 12 V; R_L = 100 Ω)		I_{GT}	2.0	7.0	30	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V; R_L = 100 Ω)		V_{GT}	–	0.65	1.5	V
Gate Trigger Non-Current (Continuous dc) (V_D = 12 V; R_L = 100 Ω)		V_{GD}	0.2	0.40	–	V
Holding Current (V_D = 12 V, Initiating Current = 200 mA, Gate Open))		I_H	3.0	15	50	mA
Latch Current (V_D = 12 V, I_G = 30 mA)		I_L	–	35	80	mA
Gate Controlled Turn-On Time (Note 5) (V_D = Rated V_{DRM}, I_G = 150 mA) (I_{TM} = 24 A Peak)		V_{GT}	–	1.0	–	µs

Revised: 07/15/19

Dynamic Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Critical Rate of Rise of Off–State Voltage (V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)	dv/dt	10	–	–	V/µs
Critical Rate of Rise of On–State Current I_G = 150 A T_J = 125°C	di/dt	–	–	75	A/µs

3. Pulse duration ≤ 300 µs, duty cycle ≤ 2%.
4. Ratings apply for tw = 1 ms. See Figure 1 for I_{TM} capability for various durations of an exponentially decaying current waveform. tw is defined as 5 time constants of an exponentially decaying current pulse.
5. The gate controlled turn-on time in a crowbar circuit will be influenced by the circuit inductance.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current

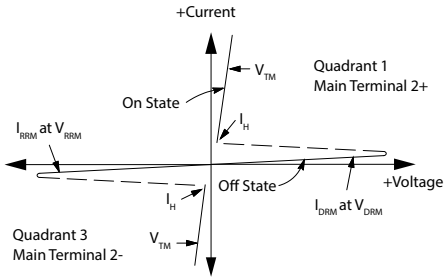


Figure 1. Current Derating

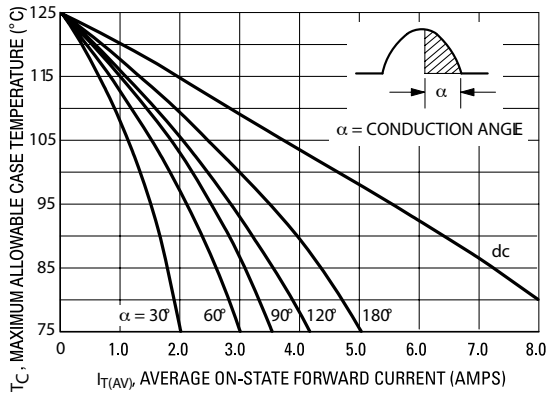


Figure 2. On–State Power Dissipation

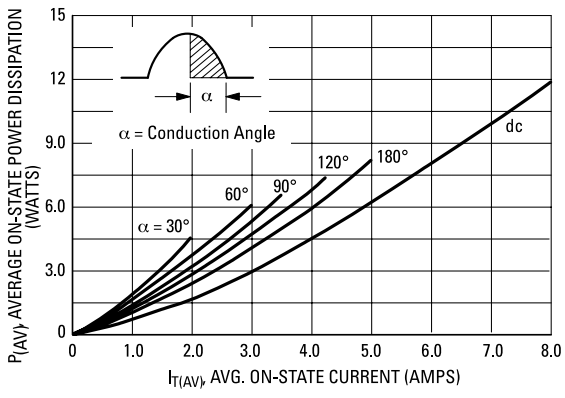


Figure 3. Typical Gate Trigger Current vs Temperature

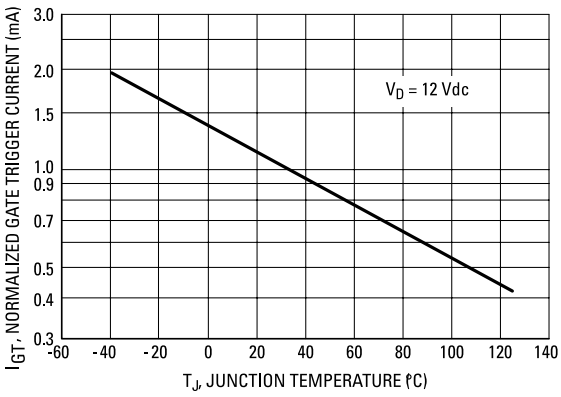


Figure 4. Typical Gate Trigger Voltage vs Temperature

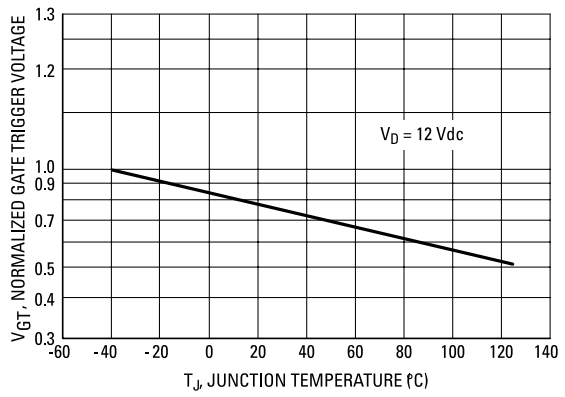
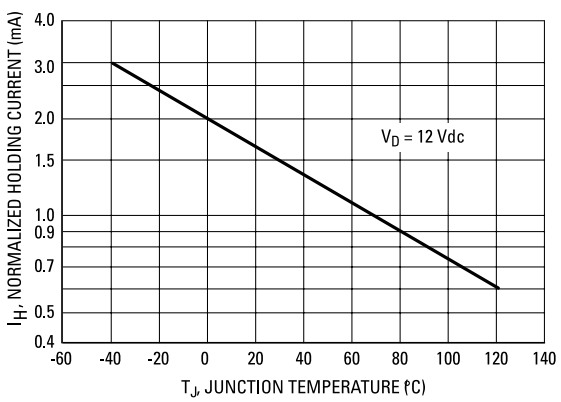


Figure 5. Typical Holding Current vs Temperature

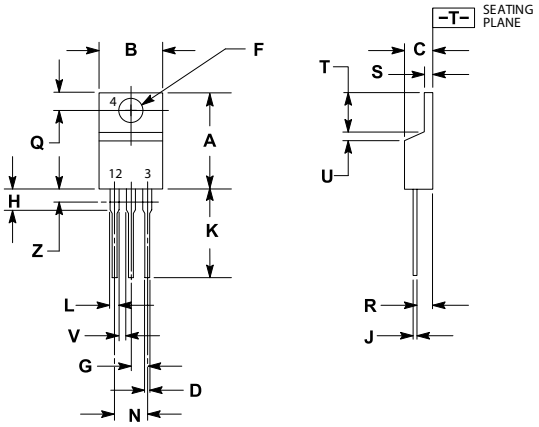


Revised: 07/15/19

Thyristors

Surface Mount – 50V - 400V > MCR218-2G, MCR218-4G, MCR218-6G

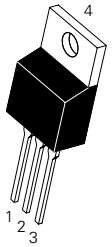
Dimensions



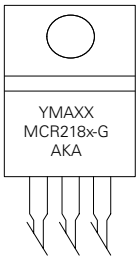
Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.590	0.620	14.99	15.75
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
H	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

Part Marking System



TO-220AM
Case 221A
Style 12



MCR218x	=Device Code
x	=2, 4, or 6
Y	=Year
M	=Month
A	=Assembly Site
AKA	=Diode Polarity
G	=Pb-Free Package

Pin Assignment	
1	Cathode
2	Anode
3	Gate
4	Anode

Ordering Information

Device	Package	Shipping
MCR218–2G	TO-220AB (Pb-Free)	500 Units / Box
MCR218–4G		
MCR218-6G		

Revised: 07/15/19

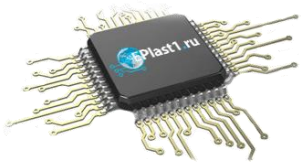
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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